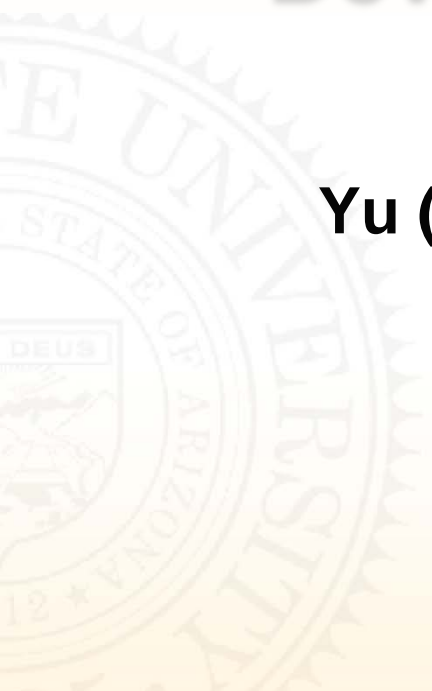


Neuromorphic Computing with Resistive Synaptic Arrays: Devices, Circuits and Systems

Yu (Kevin) Cao, Shimeng Yu, Jae-sun Seo

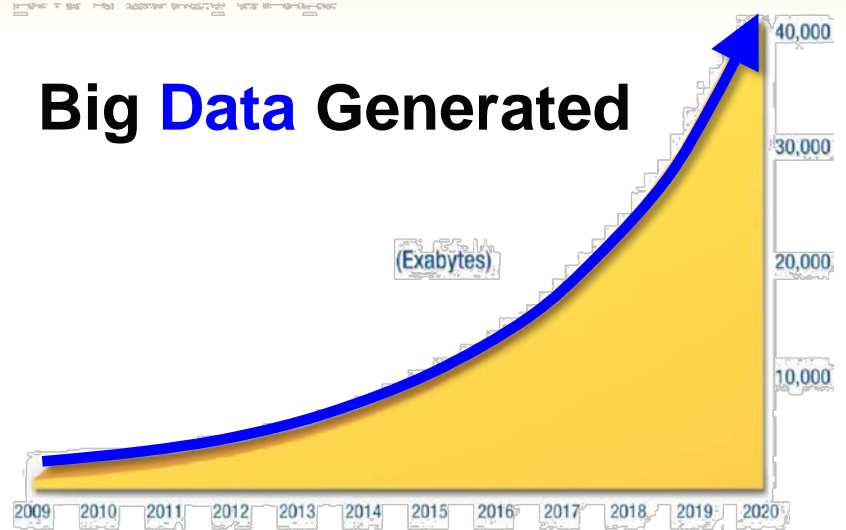
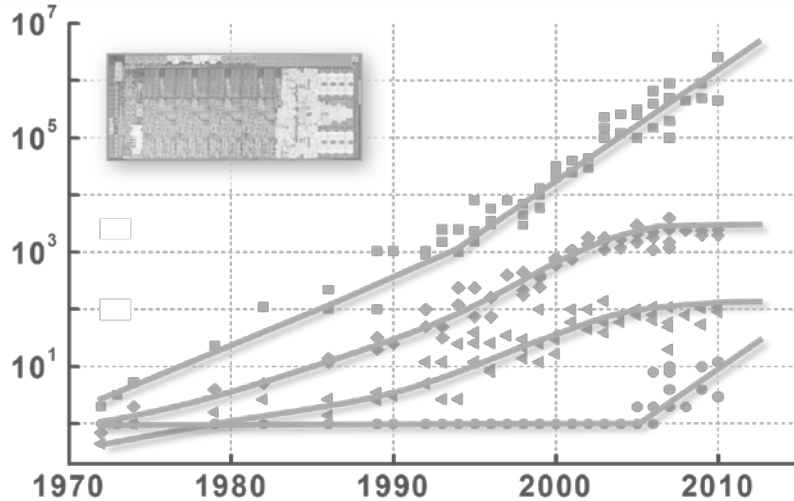
School of ECEE, Arizona State University



Outline

- Learning On-a-chip:
Synaptic Devices and the Crosspoint Array
- Non-ideal **Device** Effects on Learning Accuracy
- Peripheral **Circuits** and Parallel Operation
- A **System**-level Benchmark Simulator
- Summary and Discussion

From Data to Information



Useful If Tagged
and Analyzed



Tagged



Big Gap in Information Analysis!

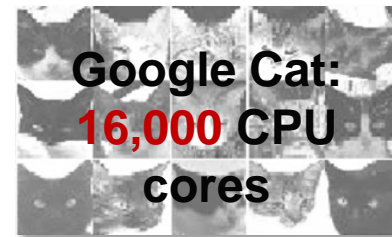
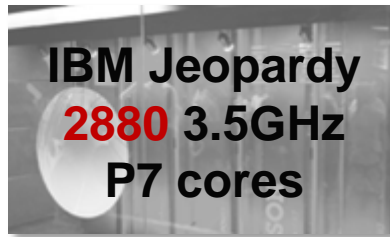
Analyzed



[IDC, December 2012]

Learning On-a-chip

- Deep learning in the cloud: expensive **computation**, **huge training** data, low **energy** efficiency, high precision

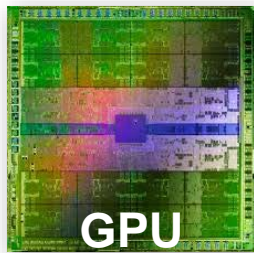


- Edge computing needs novel hardware / algorithms
 - **Local** to the sensor, **real-time**, **reliable**, low-power
 - **On-line**, personalized learning with continuous data

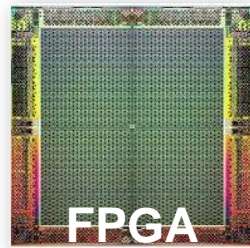


Acceleration Need

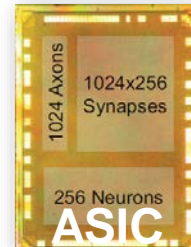
- $10^3 - 10^5$ speedup required to achieve real-time training of HD images at 30 frames/second



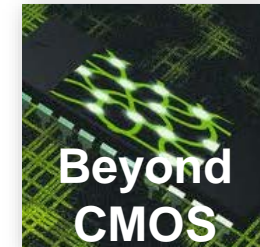
10 – 30 X



10 – 50 X

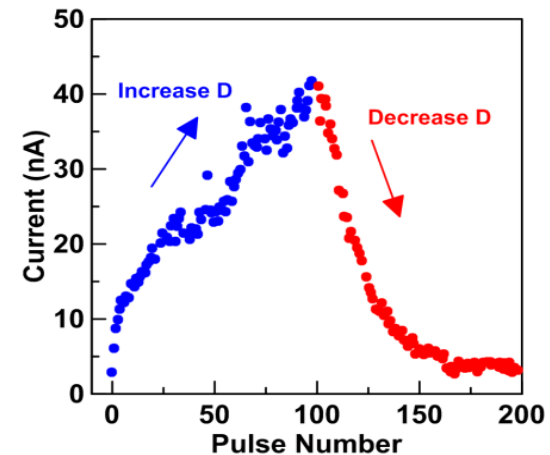
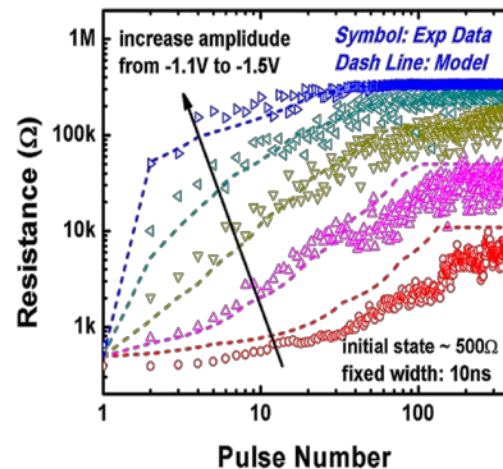
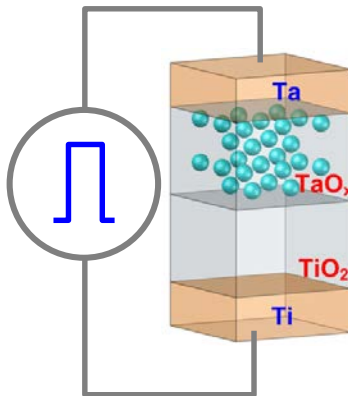


$10^2 - 10^3$ X



$>10^3$ X

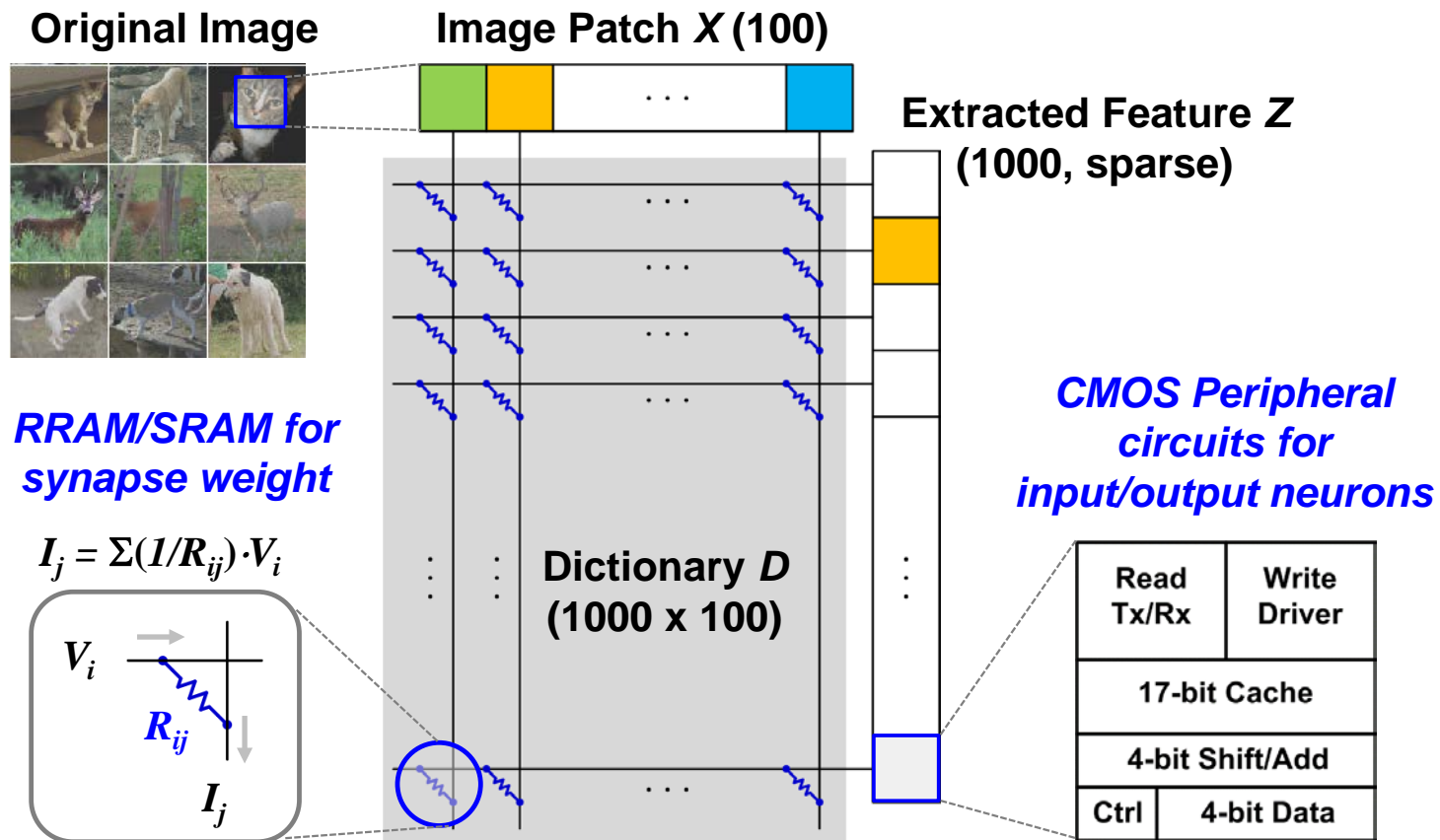
- Device beyond CMOS: RRAM to emulate the synapse



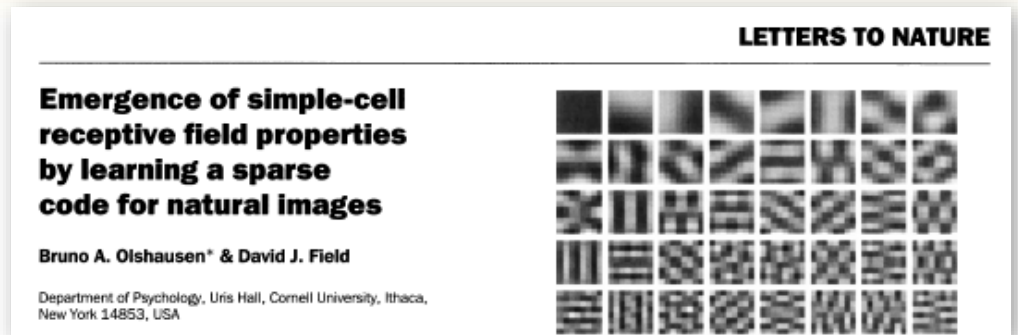
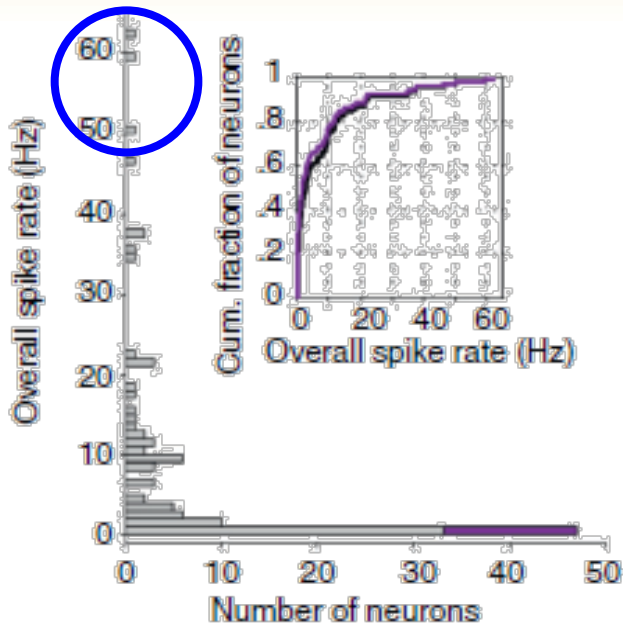
[S. H. Jo *et al.*, Nano Letter 2009]

Resistive Crosspoint Array

- A biomimetic solution: RRAM for synapse, crosspoint for dense interconnection; not necessarily spiking neurons



Sparse Coding



$$\min_{D,Z} \frac{1}{n} \sum_{i=1}^n \left(\underbrace{\frac{1}{2} \| D \cdot Z_i - x_i \|^2}_{\text{Reconstruction Error}} + \lambda \underbrace{|Z_i|_1}_{\text{Sparseness}} \right)$$

- High power efficiency
- No backward propagation
- Scalable to multi-layers

X : input vector

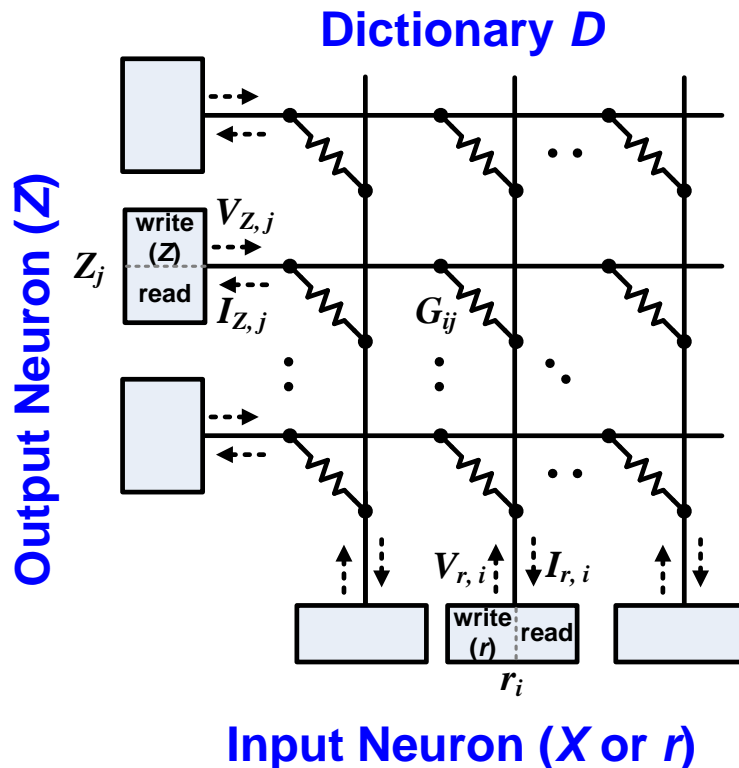
Z : feature vector (output)

D : dictionary (weight matrix)

[D. H. O'Connor *et al.*, Neuron 2010; B. A. Olshausen, D. J. Field, Nature 1996]

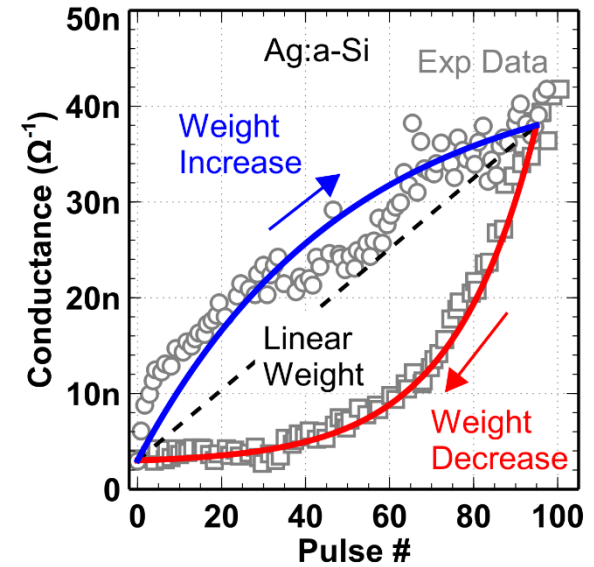
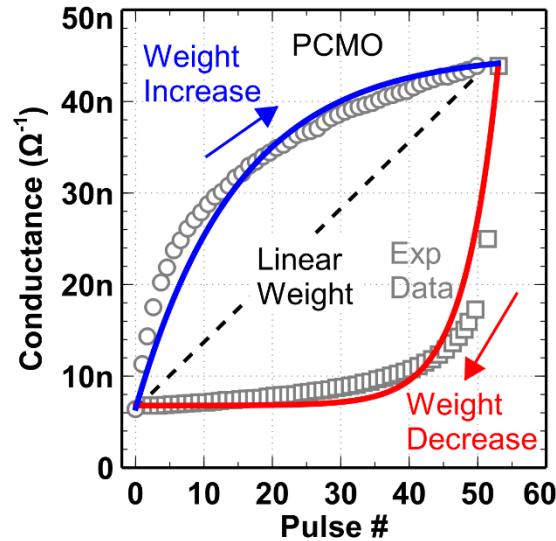
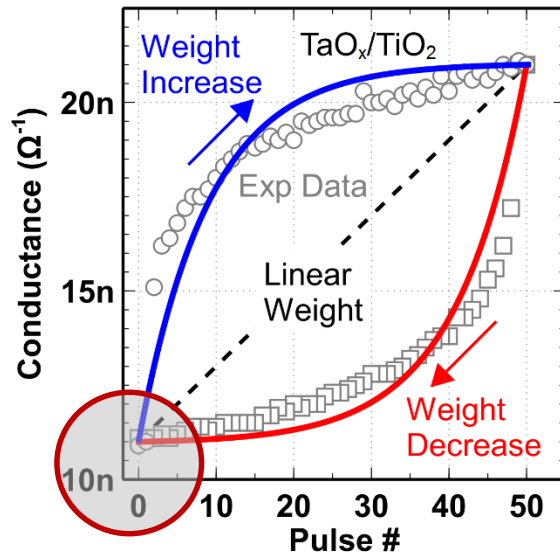
Analog Memory and Computing

- All cells are DC connected, no sneak path for read
- The value of Z , X (or r) represented by the number of voltage pulses; D by the RRAM conductance



Task	Operations
$D \cdot Z$	$I_{r,i} = \sum_j G_{ij} \cdot V_{Z,j}$
$D^T \cdot r$	$I_{Z,j} = \sum_i G_{ij} \cdot V_{r,i}$
D update	$\Delta G_{ij} = \eta \cdot r \cdot Z$

Realistic Device Properties

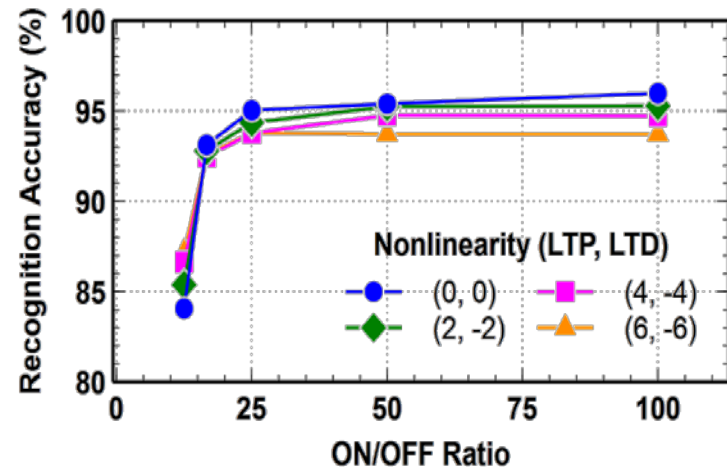
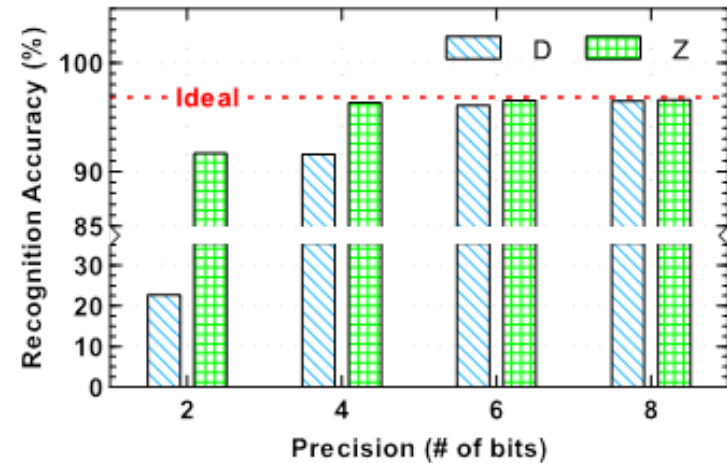
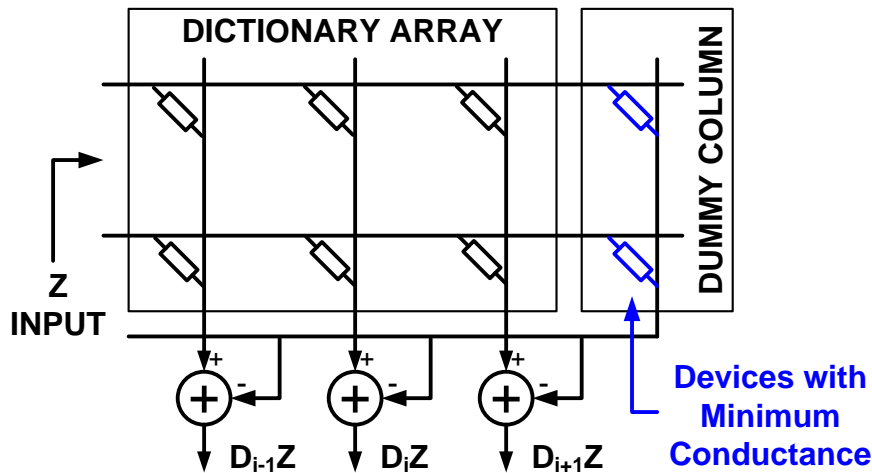


- Non-zero off-state conductance; limited levels / precision
- Device variations; nonlinearity in weight update
- Experiment with unsupervised **sparse coding + MNIST** to study their impact on learning accuracy

[B. A. Olshausen, D. J. Field, Nature 1996]

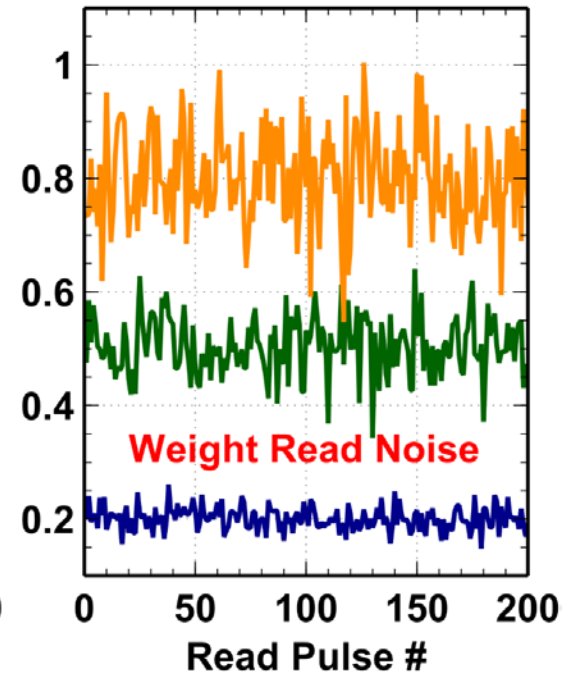
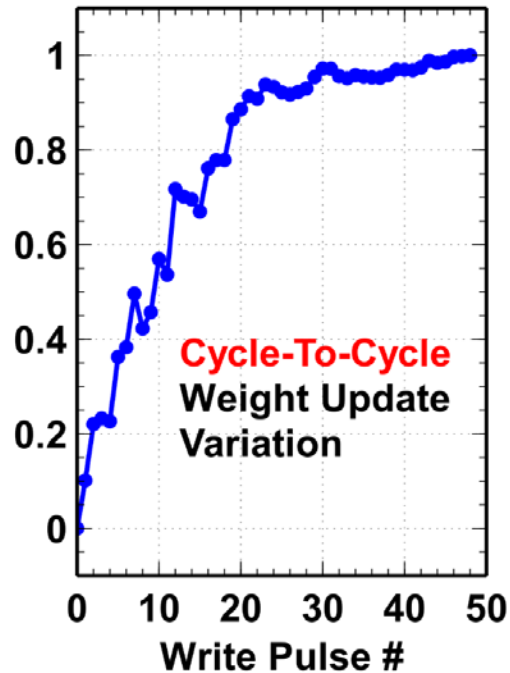
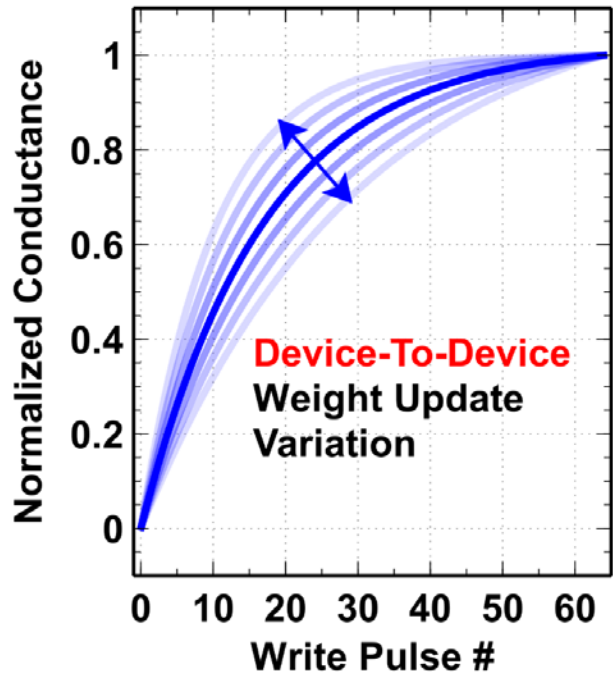
Non-zero Off-state and Precision

- Solution: spatial redundancy to solve non-zero off-state
- Fixed-point computing
 - Weight (D): **6 bits (64 levels)**
 - Output (Z): 4 bits
 - On/off ratio needs to be > 25

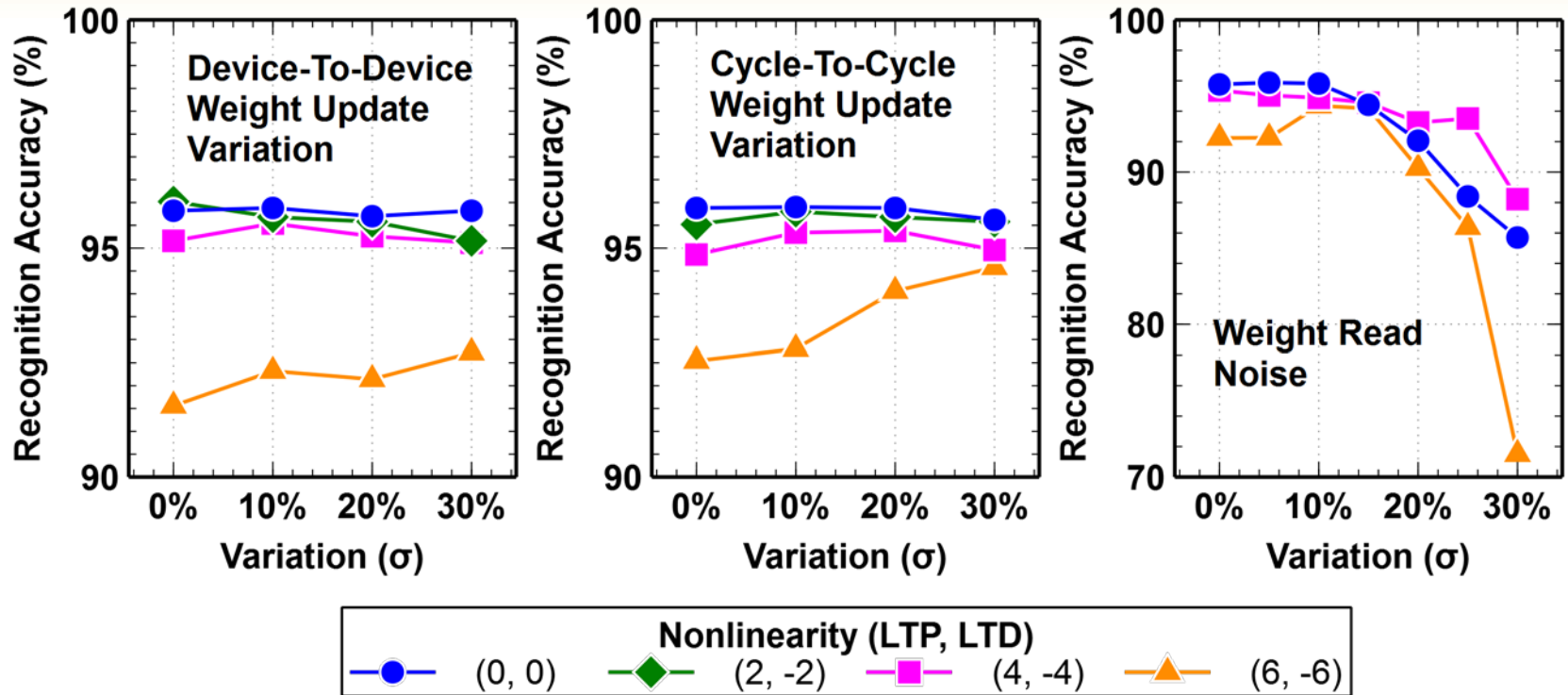


Device Variations

- Weight update variation: device-to-device and cycle-to-cycle
 - Device nonlinearity has moderate impact on the accuracy
- Weight read noise



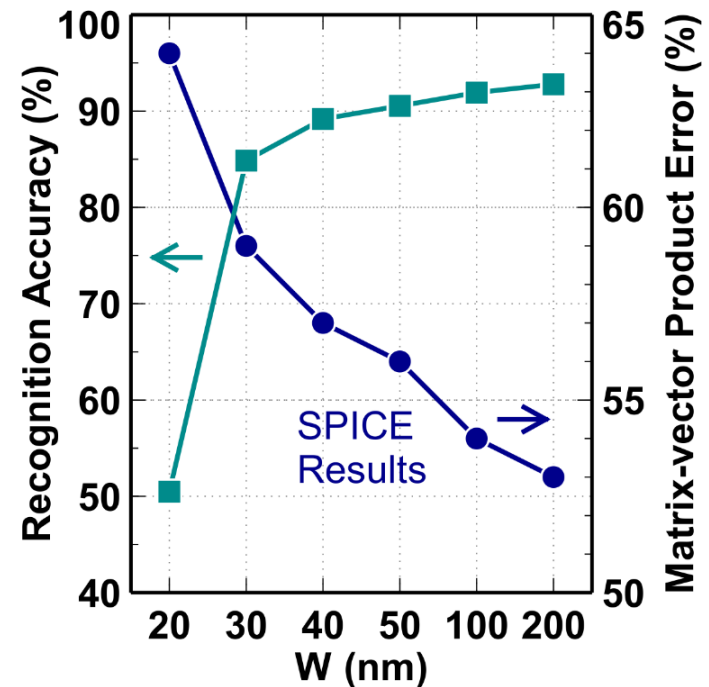
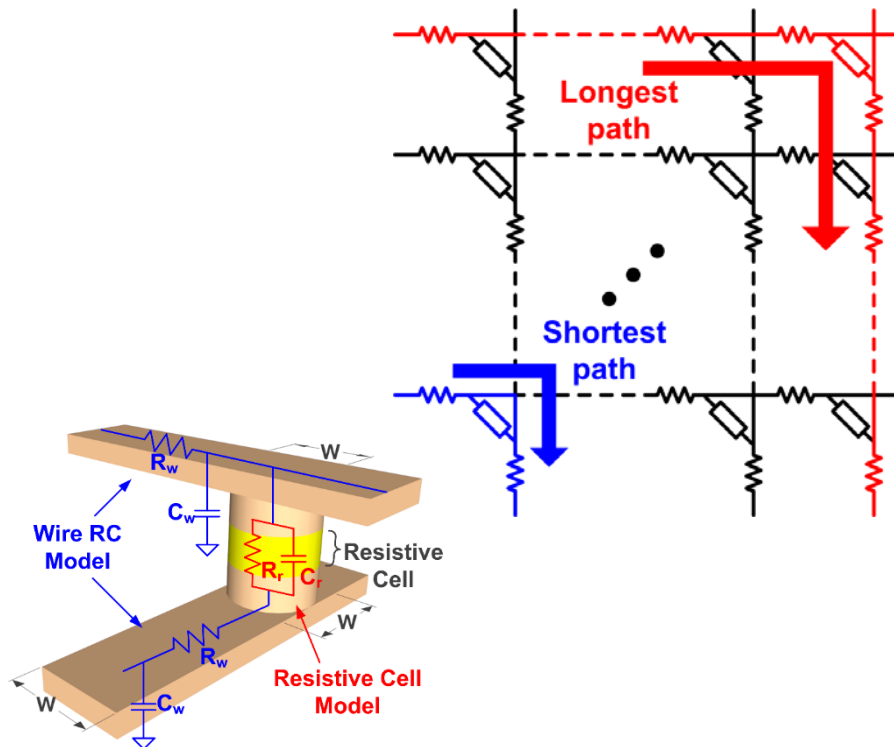
Impact on the Accuracy



- Impact of weight update variation: **moderate**
- Impact of weight read noise: **significant**
- Solution: multiple cells to minimize the variation

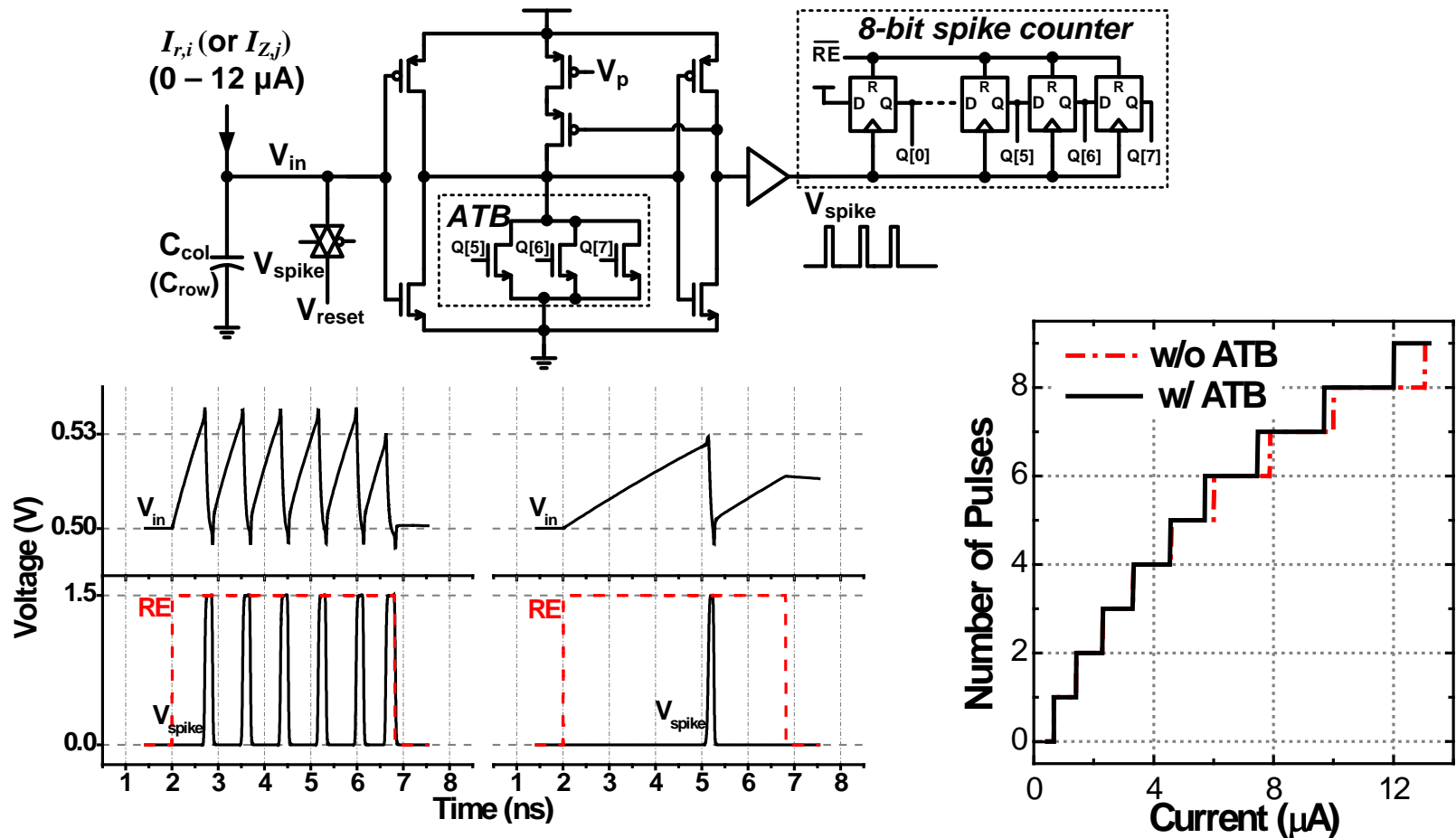
Interconnect Resistance

- Wire resistance is in series with RRAM resistance
 - RC delay is not an issue
- Solution: scaling up the wire



Neuron Circuits: Parallel Read

- A **current-to-digital converter**, operating as the Integrate-and-Fire neuron model

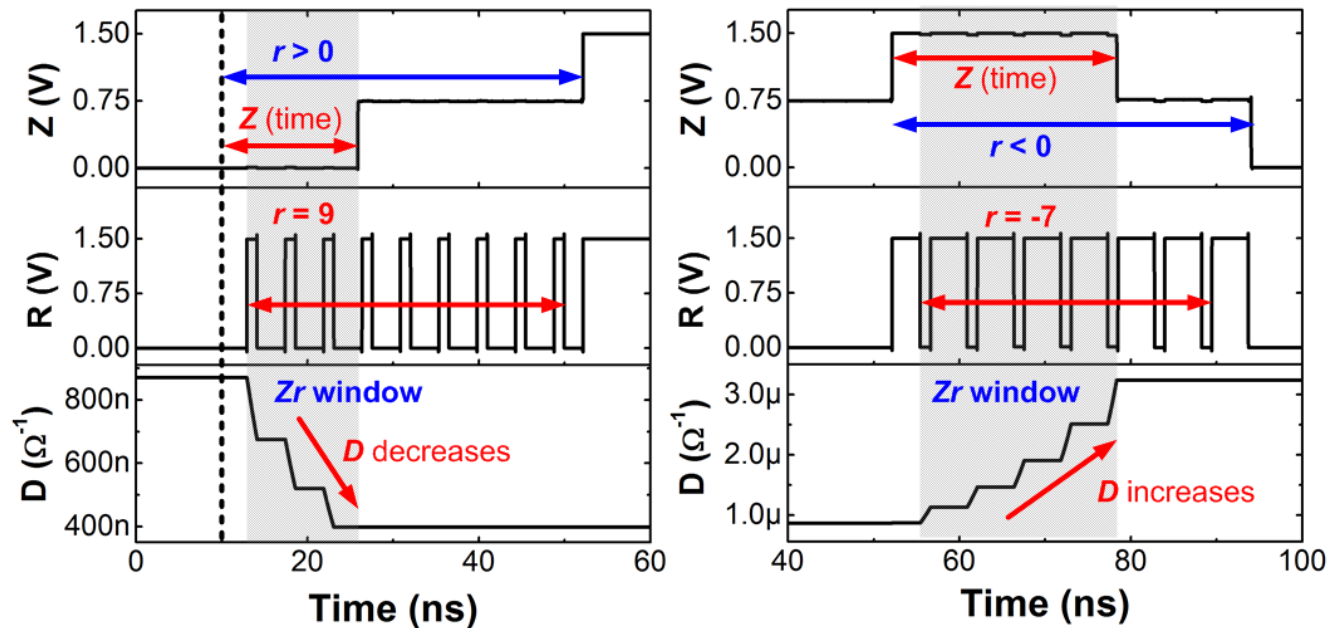


Neuron Circuits: Parallel Write

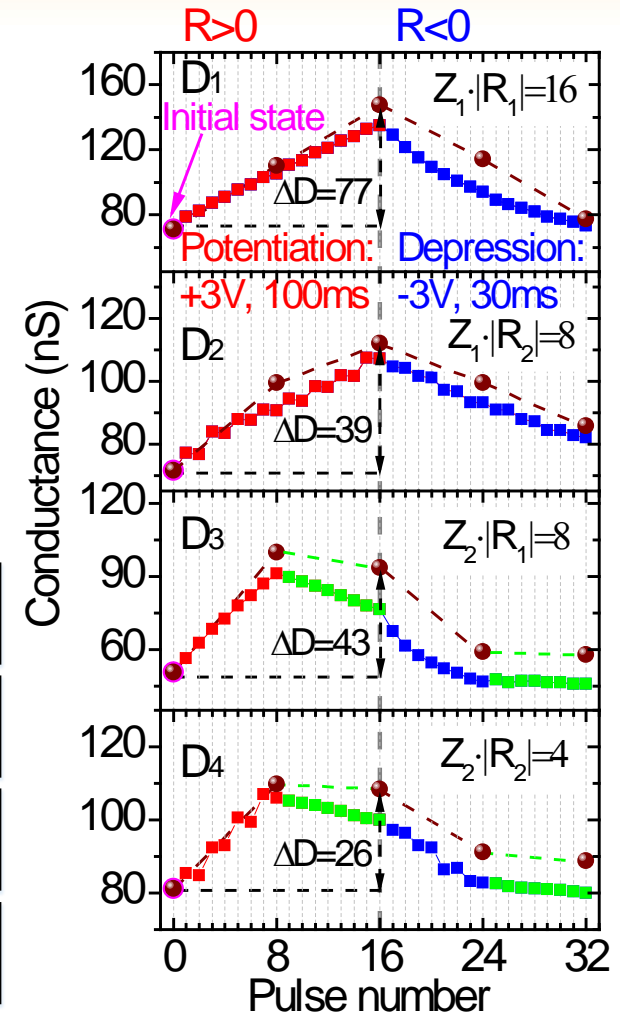
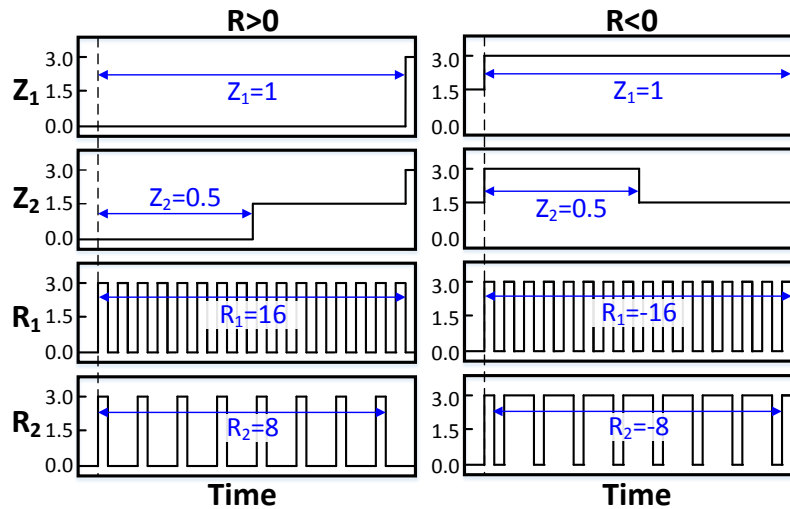
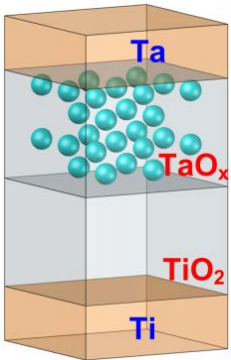
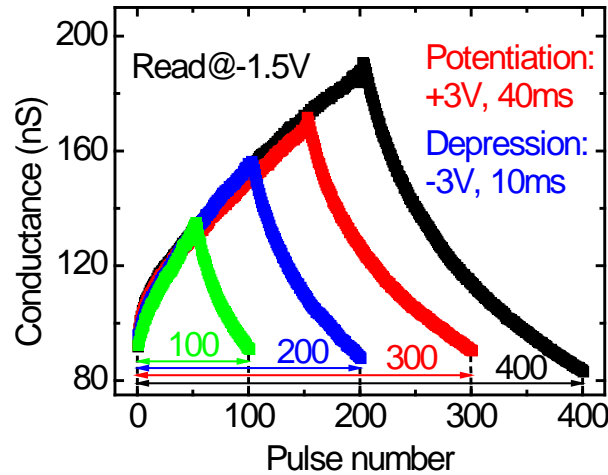
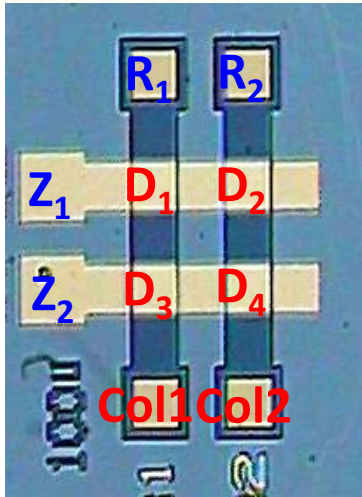
- Write RRAM through the **spiking rate** between input (X or r) and output (Z) neurons

$$\Delta G_{ij} \propto \text{pulse width} = \text{Write Time} \cdot \text{Firing Rate} = \eta \cdot Z \cdot r$$

- Z value for the time window to write
- r value for the pulse number (firing rate)

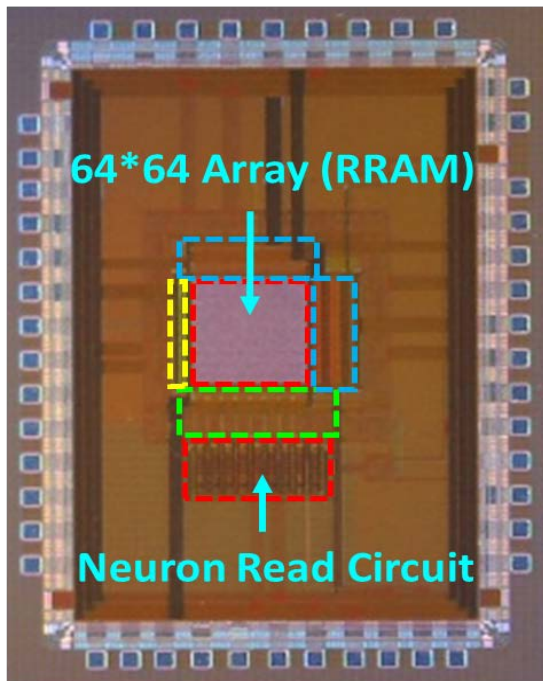


Parallel Operation: O(1)

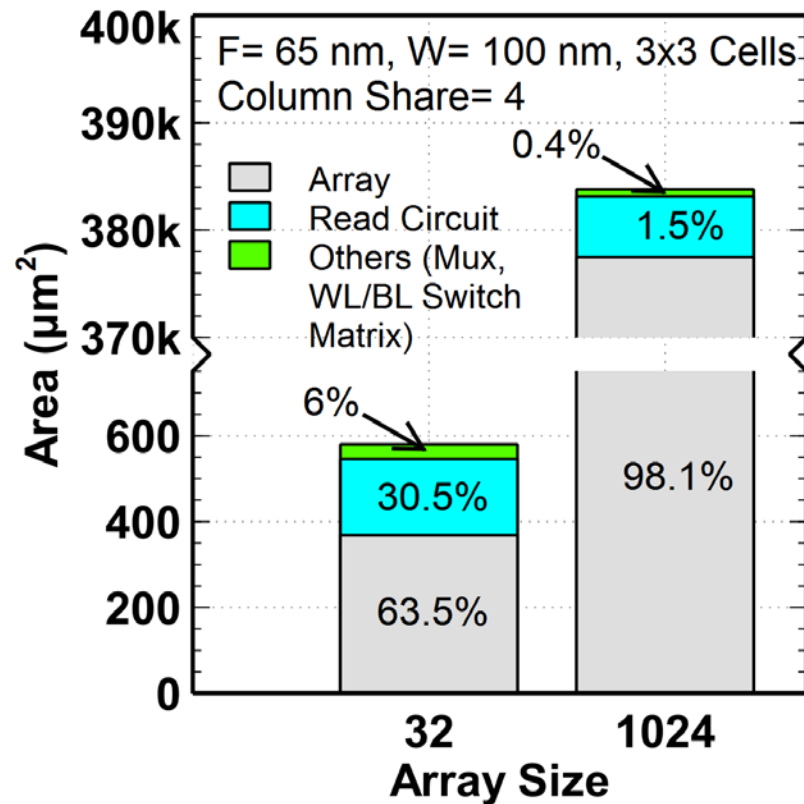


Array Size

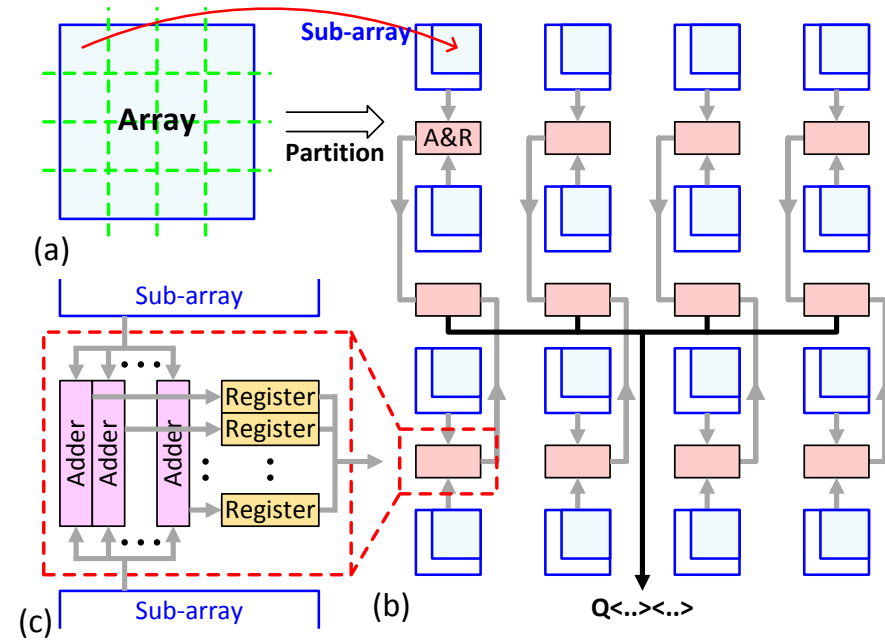
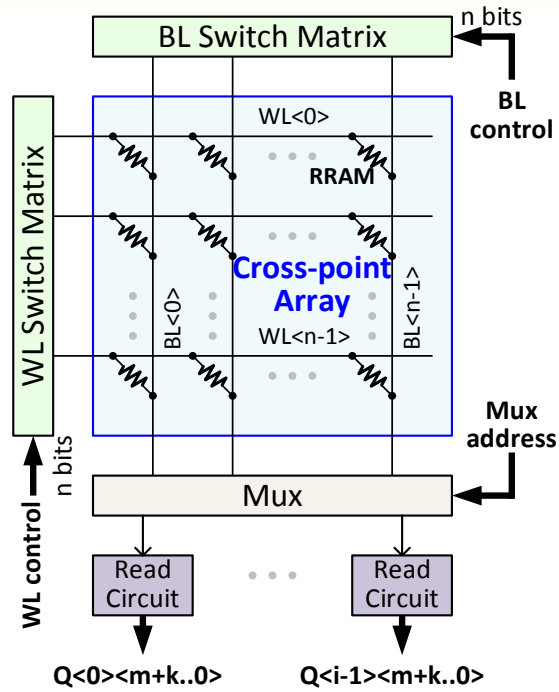
- Peripheral circuits consume significant area
- Solution: scaling up the array size; non-CMOS neurons



130nm 1T1R array



System Simulator for Benchmark



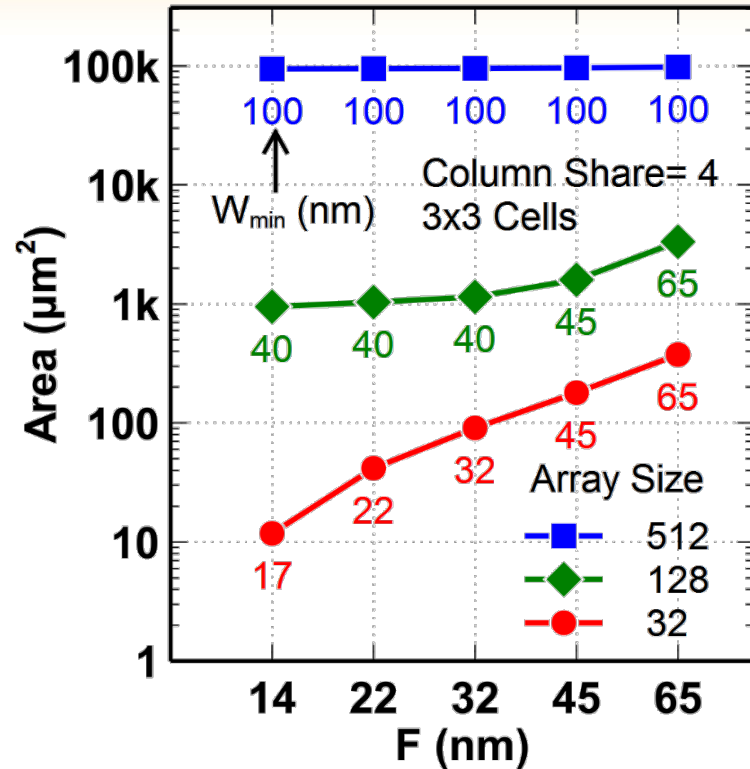
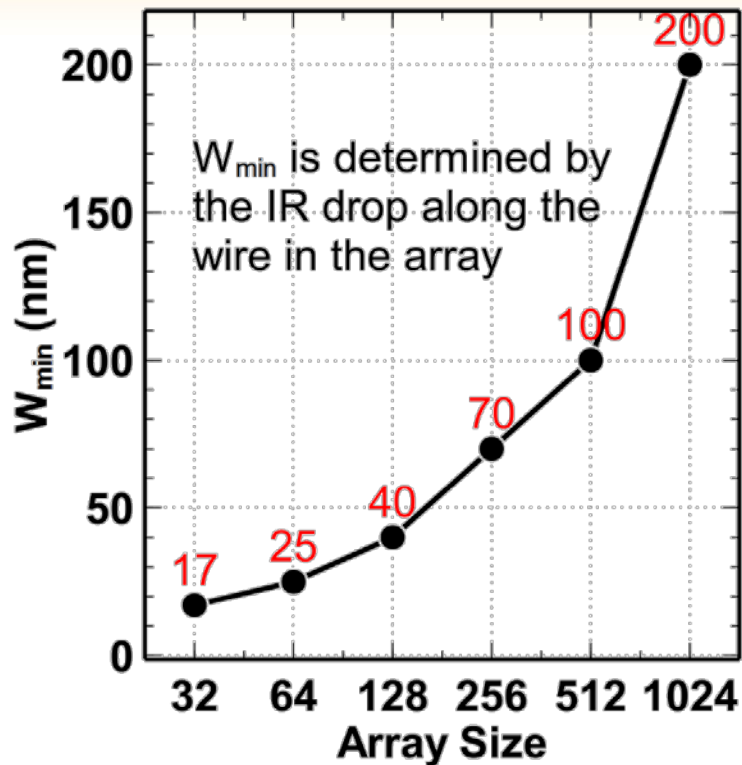
- Built on the template of CACTI and NVSim
- Metrics include area, latency, leakage power, dynamic power, etc. for a given array size, device type and node

Example: A 256 x 256 Array

Architecture (array size=256 ²)	Area	Read Latency	Read Energy	Write Latency	Write Energy	Leakage
SRAM Array (row-by-row)	39638.07 μm ²	393.38 ns	15.14 nJ	114.55 ns	1.9 nJ	3247.93 μW
1T1R Array (row-by-row)	5601.04 μm ²	75.51 ns	1.84 nJ	10311.42 ns	15.22 nJ	11.17 μW
Cross-point Array (fully parallel)	6551.49 μm ²	70.63 ns	1.68 nJ	160 ns	10.62 nJ	2.07 μW

Sparse Coding	SRAM	1T1R	Cross-point	Improvement
Update Z (200 Read)	78.7 μs	15.1 μs	14.1 μs	
Update D (1 Write)	115 ns	10.3 μs	160 ns	
Time for 1 Iteration	78.8 μs	25.4 μs	14.2 μs	5.5x

Technology Scaling



- Large array does not scale well due to wire width relaxation
- Solution: partition of large array into multiple small arrays with technology scaling

Future Needs

- Synaptic Device: variation control, read noise reduction, better endurance (habituation), more levels (>4-bit)
- Circuits and Architecture: larger array, **peripheral device/circuits**, physical design, multi-array architecture
- Neuromorphic Algorithm: brain-inspired algorithm for low precision, compact network, and high energy efficiency

